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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number	10/691,080			
Filing Date	October 22, 2003			
First Named Inventor	Barry E. Burke			
Art Unit	2818			
Examiner Name	C. Luu			
Attorney Docket Number	MIT8431L			

			U. S. PATENT	DOCUMENTS	
Examiner Initials*	Cite No.1	Document Number Number-Kind Code ^{2 (f known)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
CAL	A1	^{US-} 3,728,590	04-17-1973	Kim et al.	
	A2	^{US-} 3,853,634	12-10-1974	Amelio et al.	
\neg	A3	^{US-} 5,298,448	03-29-1994	Stevens et al.	
	A4	^{US-} 4,063,992	12-20-1977	Hosack	
	A5	^{US-} 4,613,402	09-23-1986	Losee et al.	
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M	A11	^{US-} 5,760,431	06-02-1998	Savoye et al.	
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		FORE	IGN PATENT DOCU	MENTS	
Examiner Initials*	Cite No.'	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
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CODSUM	0 101 101111 14	131 10			Application Number	10/691,080
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STA	STATEMENT BY APPLICANT			PPLICANT	First Named Inventor	Barry E. Burke
(Use as many sheets as necessary)				Art Unit	2818	
			cessary)	Examiner Name	C. Luu	
Sheet	2		of	2	Attorney Docket Number	MIT8431L

_	NON PATENT LITERATURE DOCUMENTS			
Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			
B1	BROWNE et al., "A Nonoverlapping Gate Charge-Coupling Technology for Serial Memory and Signal Processing Applications," IEEE Jnl of Solid-State Circuits, Vol. SC11, No. 1, pp. 203-207, February 1976.			
B2	KAPOOR, "Charge-Coupled Devices with Submicron Gaps," IEEE Electron Device Ltrs., Vol. EDL-2, No. 4, pp. 92-94, April 1981.			
В3	SLOTBOOM et al., "Submicron CCD memory structures fabricated by electron-beam lithography," Proc. IEDM '84, paper 11.6, pp. 308-311, 1984.			
B4	GAJAR et al., "An ionic liquid-channel field-effect transistor," J. Electrochem. Soc., V. 139, No. 10, pp. 2833-2840, October 1992.			
B5	YAMADA et al., "Driving Voltage Reduction in a Two-Phase CCD by Suppression of Potential Pockets in Inter-Electrode Gaps," IEEE Trans. on Electron Devices, V. 44, No. 10, pp. 1580-1587, October 1997.			
86	OKADA et al., "Performance of FT-CCD image sensor with Single Layer Poly-Silicon Electrode," 1999 IEEE Workshop on Charge-Coupled Devices and Advanced Imager Sensors, pp. 219-222, Nagano, Japan, June 1999.	·		
87	BURKE et al., "Charge-coupled device made with a single polysilicon level," Massachusetts Institute of Technology Lincoln Laboratory Solid State Research Quarterly Technical Report, pp. 31-37, March 1, 2002.			
	B1 B2 B3 B4 B5 B6	Cite No.1 Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. BROWNE et al., "A Nonoverlapping Gate Charge-Coupling Technology for Serial Memory and Signal Processing Applications," IEEE Jnl of Solid-State Circuits, Vol. SC11, No. 1, pp. 203-207, February 1976. KAPOOR, "Charge-Coupled Devices with Submicron Gaps," IEEE Electron Device Ltrs., Vol. EDL-2, No. 4, pp. 92-94, April 1981. SLOTBOOM et al., "Submicron CCD memory structures fabricated by electron-beam lithography," Proc. IEDM '84, paper 11.6, pp. 308-311, 1984. GAJAR et al., "An ionic liquid-channel field-effect transistor," J. Electrochem. Soc., V. 139, No. 10, pp. 2833-2840, October 1992. YAMADA et al., "Driving Voltage Reduction in a Two-Phase CCD by Suppression of Potential Pockets in Inter-Electrode Gaps," IEEE Trans. on Electron Devices, V. 44, No. 10, pp. 1580-1587, October 1997. OKADA et al., "Performance of FT-CCD image sensor with Single Layer Poly-Silicon Electrode," 1999 IEEE Workshop on Charge-Coupled Devices and Advanced Imager Sensors, pp. 219-222, Nagano, Japan, June 1999. BURKE et al., "Charge-coupled device made with a single polysilicon level," Massachusetts Institute of		

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